

DOCKET NO.: BUR920040182US1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Chen *et al.*

Examiner: Whitmore, Stacy

Serial No.: 10/711,418

Art Unit: 2825

Filed: 9/17/2004

Title: **NON-DESTRUCTIVE EVALUATION OF MICROSTRUCTURE AND
INTERFACE ROUGHNESS OF ELECTRICALLY CONDUCTIVE LINES IN
SEMICONDUCTOR INTEGRATED CIRCUITS IN DEEP SUB-MICRON
REGIME**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

OFFICE ACTION RESPONSE

Sir:

This communication is in response to the Office Action mailed October 23, 2006.

On Friday, December 15, 2006, Applicants' representative Khoi D. Nguyen and Examiner Stacy Whitmore talked over the phone and came to the following agreements:

(A) there are 20 claims,

(B) a flow chart showing the steps of claim 1 is required,

(C) a new title of the invention suggested by representative Khoi D. Nguyen is acceptable,

and

(D) an additional step (e) to claim 1 suggested by representative Khoi D. Nguyen is acceptable.